

# UV-B Sensor

## GUVB-T11SD



- Features**
- Aluminium Gallium Nitride Based Material
  - Schottky-type Photodiode
  - Photovoltaic Mode Operation
  - Good Visible Blindness
  - High Responsivity & Low Dark Current



- Applications**
- Pure UV-B Monitoring
  - UV Index Monitoring

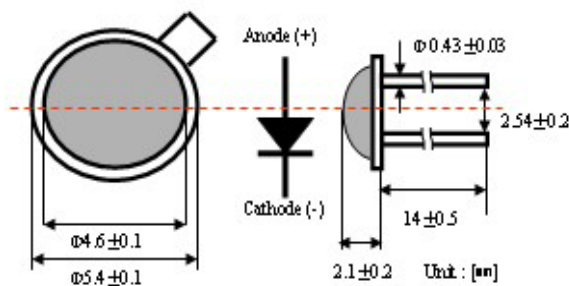
### Absolute Maximum Ratings

Parameter	Symbol	Min.	Max.	Unit	Remark
Storage Temperature	$T_{st}$	-40	90		
Operating Temperature	$T_{op}$	-30	85		
Reverse Voltage	$V_{r, max.}$		3	V	
Forward Current	$I_{f, max.}$		1	mA	
Soldering Temperature	$T_{sol}$		260		within 10 sec.

### Characteristics (at 25 °C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Dark Current	$I_d$			1	nA	$V_r = 0.1$ V
Photo Current	$I_{ph}$		146		nA	UVB Lamp, $1\text{mW}/\text{cm}^2$
Temperature Coefficient	$I_{tc}$		0.05		%/°C	UVB Lamp
Responsivity	R		0.16		A/W	$\lambda = 300$ nm, $V_r = 0$ V
Spectral Detection Range	$\lambda$	230		320	nm	
Breakdown Voltage	$V_{BR}$		5		V	$I_r = 1$ $\mu$ A

### Outline Diagrams and Dimensions



### Responsivity Curve

